

### Description

The LM8S10NP04 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

$V_{DS} = 40V$   $I_D = 9.8A$

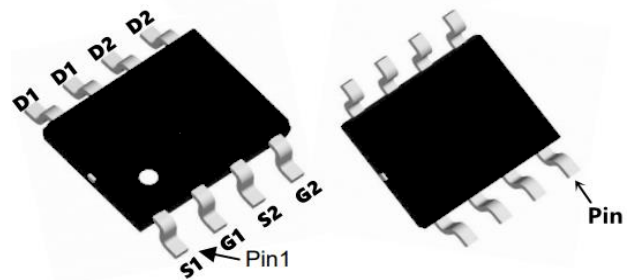
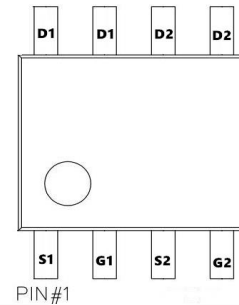
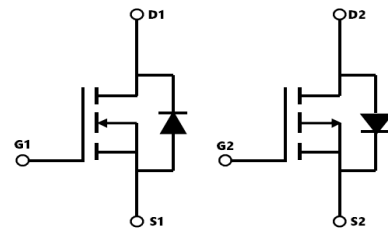
$R_{DS(ON)} < 26m\Omega$  @  $V_{GS}=10V$  (Type: 17.5m $\Omega$ )

$V_{DS} = -40V$   $I_D = -7.5A$

$R_{DS(ON)} < 45m\Omega$  @  $V_{GS}=-10V$  (Type: 38m $\Omega$ )

### Application

- Wireless charging
- Boost driver
- Brushless motor



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
LM8S10NP04	SOP-8	LM8S10NP04 XXX YYYY	3000

### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
$V_{DS}$	Drain-Source Voltage	40	-40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9.8	-7.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.2	-4.8	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	23	-22	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	16.2	39	mJ
$I_{AS}$	Avalanche Current	18	-28	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	1.67	1.67	W
$T_{STG}$	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	75		$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	30		$^\circ C/W$

## N-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	44	---	V
$\Delta BVDSS/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.034	---	V/ $^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=5A$	---	17.5	26	m $\Omega$
		$V_{GS}=4.5V, I_D=4A$	---	25.0	35	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.56	---	mV/ $^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=5A$	---	14	---	S
Rg	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.6	---	$\Omega$
Qg	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=5A$	---	5.5	---	nC
Qgs	Gate-Source Charge		---	1.25	---	
Qgd	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=20V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	8.9	---	ns
Tr	Rise Time		---	2.2	---	
Td(off)	Turn-Off Delay Time		---	41	---	
Tf	Fall Time		---	2.7	---	
Ciss	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	593	---	pF
Coss	Output Capacitance		---	76	---	
Crss	Reverse Transfer Capacitance		---	56	---	
Is	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	6.1	A
ISM	Pulsed Source Current <sup>2,5</sup>		---	---	23	A
VSD	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

### Note :

- 1、 The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width  $\cong 300\mu s$  , duty cycle  $\cong 2\%$
- 3、 The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=10A$
- 4、 The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 5、 The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

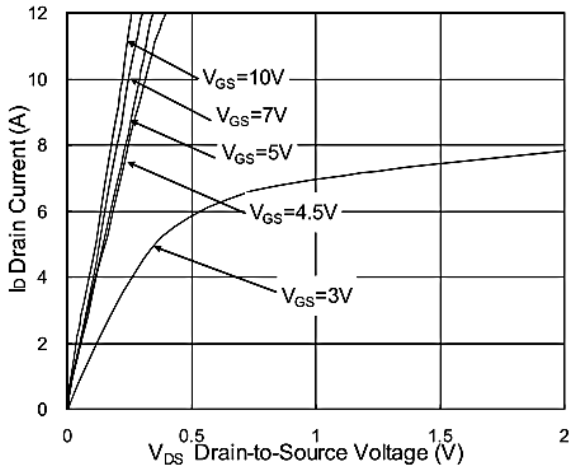
## P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-40	-44	---	V
ΔBVDSS/ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 °C, I <sub>D</sub> =-1mA	---	-0.02	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A	---	38	45	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	48	60	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.6	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	3.72	---	mV/°C
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6A	---	13	---	S
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6A	---	11.5	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.5	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.3	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-1A	---	22	---	ns
T <sub>r</sub>	Rise Time		---	15.7	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	59	---	
T <sub>f</sub>	Fall Time		---	5.5	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	1415	---	pF
C <sub>oss</sub>	Output Capacitance		---	134	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	102	---	
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-6	A
ISM	Pulsed Source Current <sup>2,5</sup>		---	---	-22	A
VSD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V

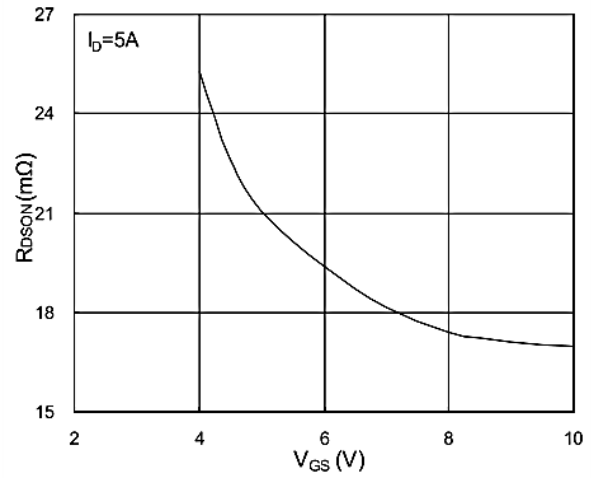
### Note :

- 1、 The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed, pulse width ≅ 300us, duty cycle ≅ 2%
- 3、 The EAS data shows Max. rating. The test condition is V<sup>DD</sup>=-25V, V<sup>GS</sup>=-10V, L=0.1mH, I<sup>AS</sup>=-10A
- 4、 The power dissipation is limited by 150 °C junction temperature
- 5、 The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

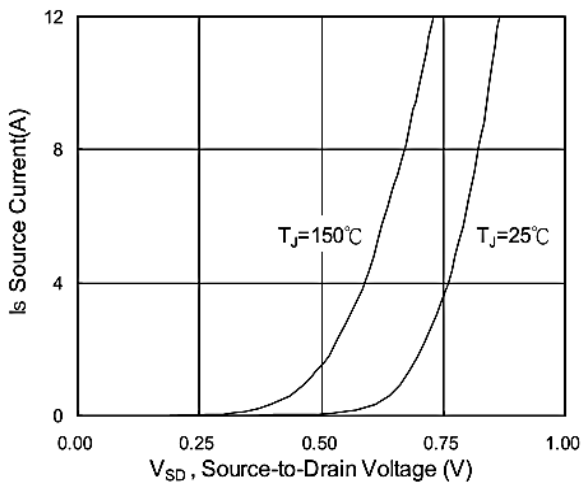
**N-Channel Typical Characteristics**



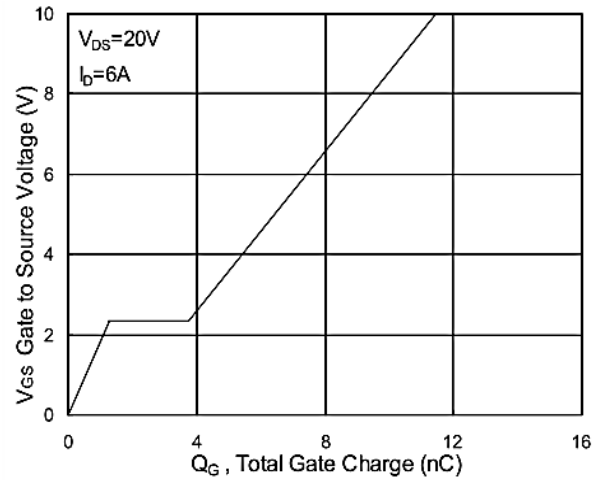
**Fig.1 Typical Output Characteristics**



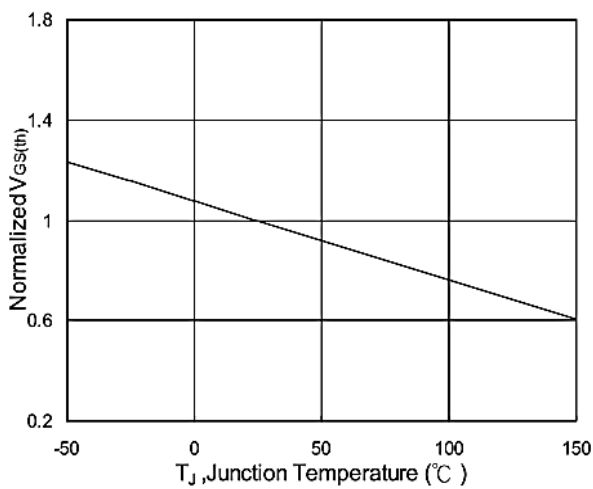
**Fig.2 On-Resistance vs. G-S Voltage**



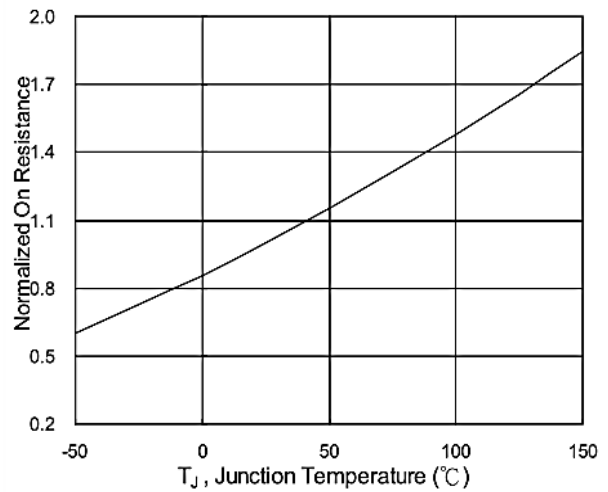
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

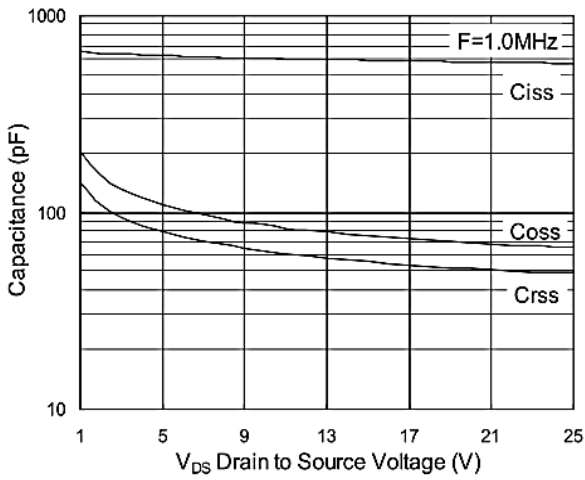


Fig.7 Capacitance

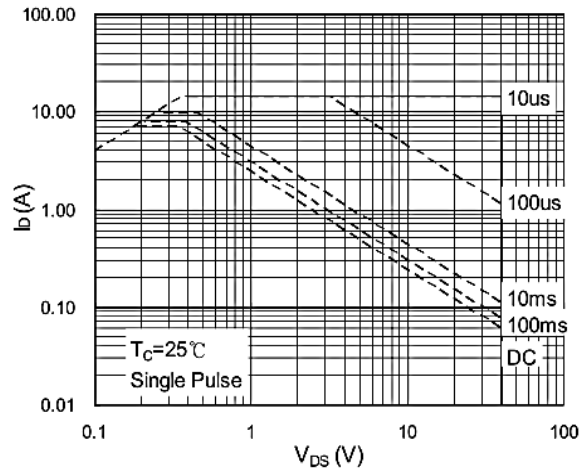


Fig.8 Safe Operating Area

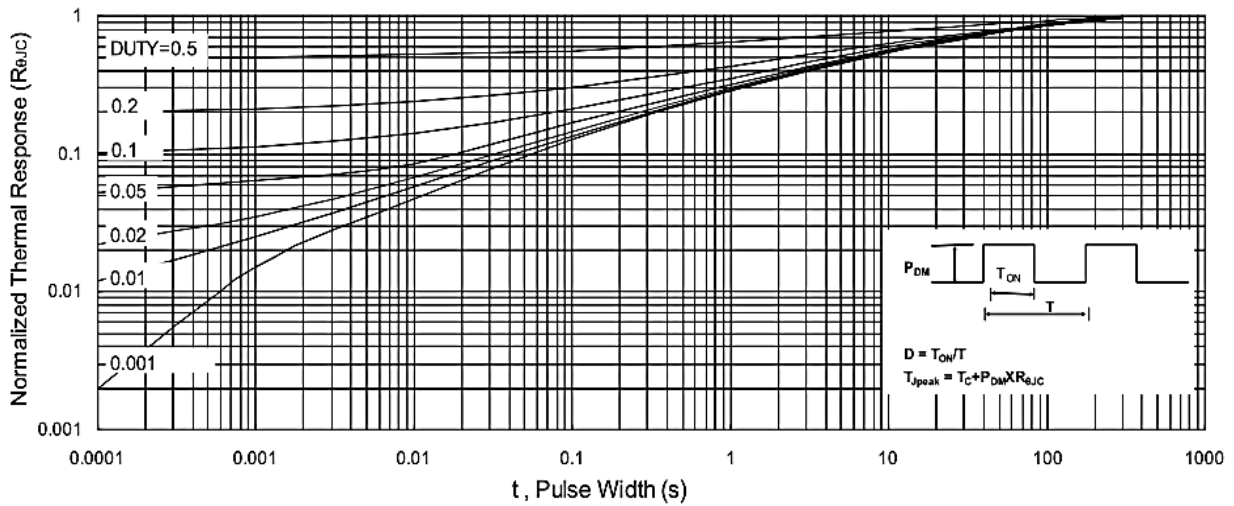


Fig.9 Normalized Maximum Transient Thermal Impedance

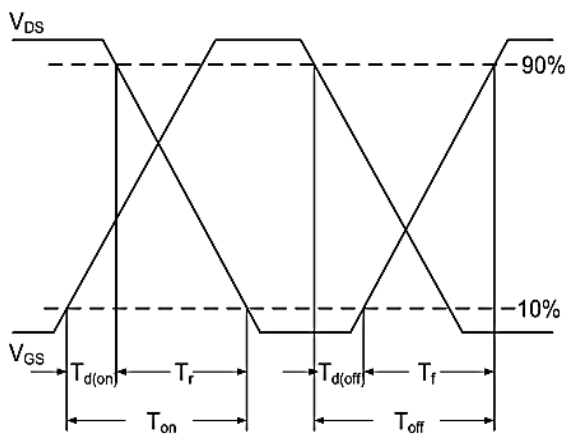


Fig.10 Switching Time Waveform

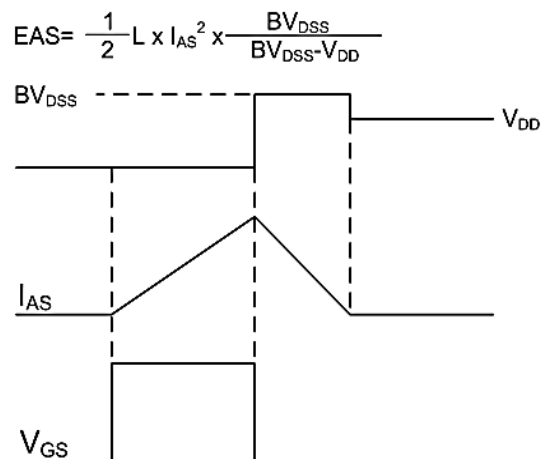
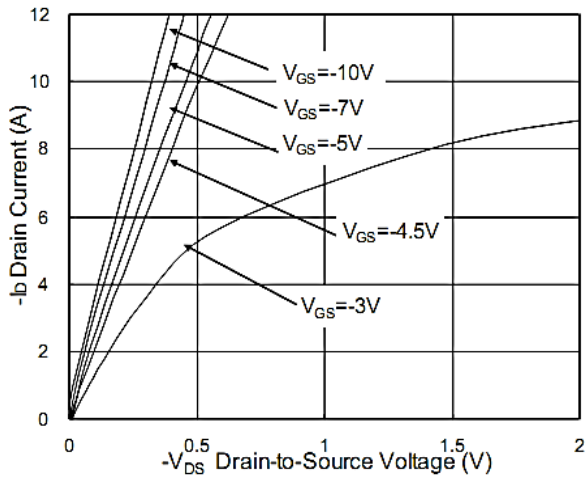
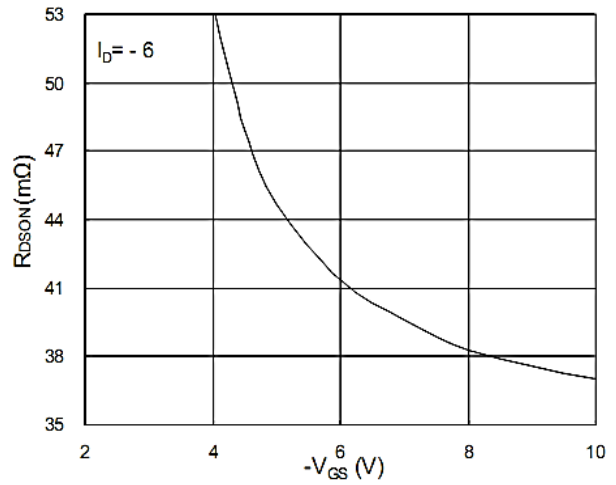


Fig.11 Unclamped Inductive Waveform

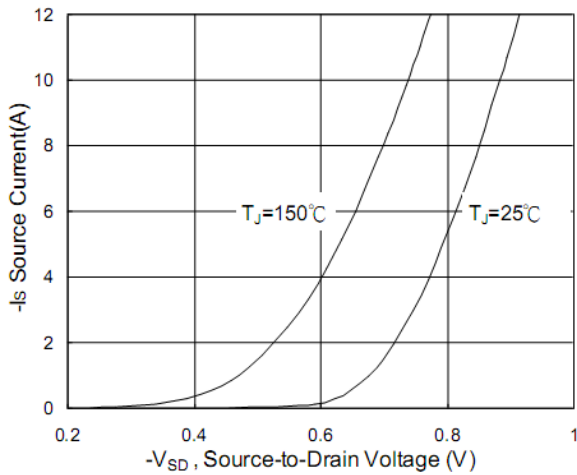
**P-Channel Typical Characteristics**



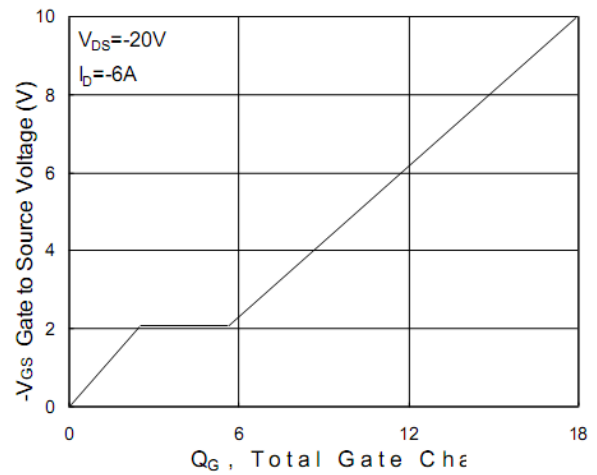
**Fig.1 Typical Output Characteristics**



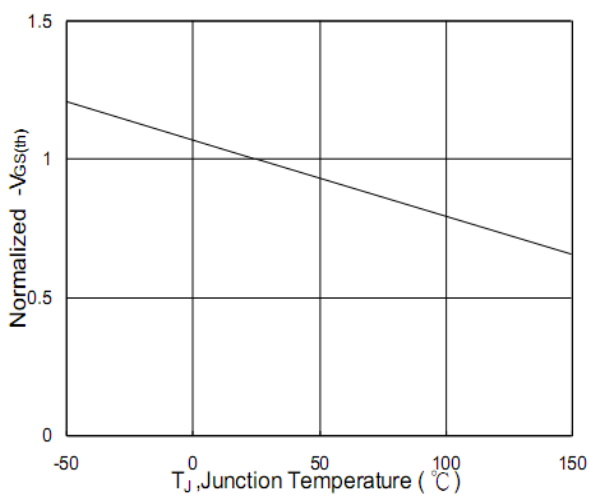
**Fig.2 On-Resistance vs. G-S Voltage**



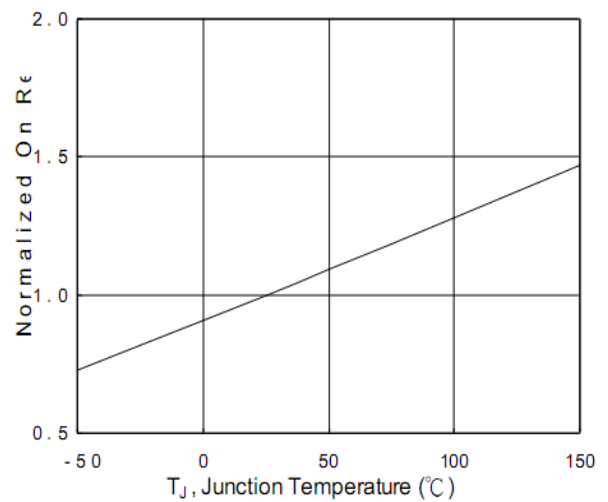
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

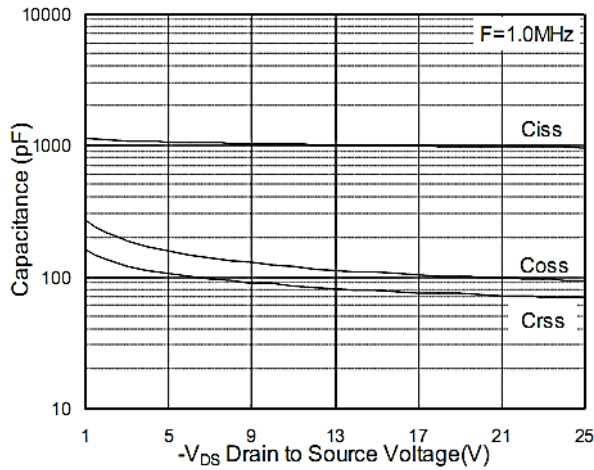


Fig.7 Capacitance

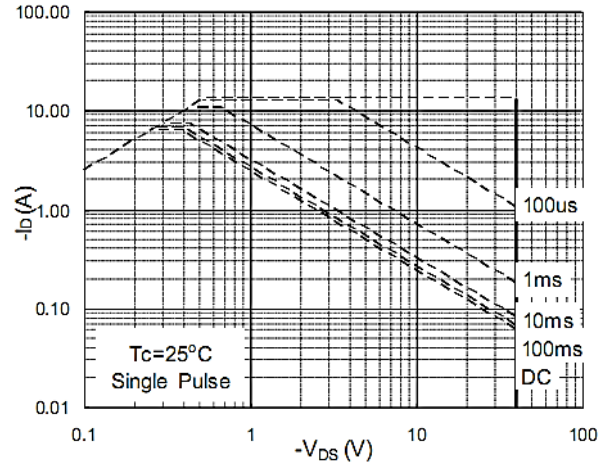


Fig.8 Safe Operating Area

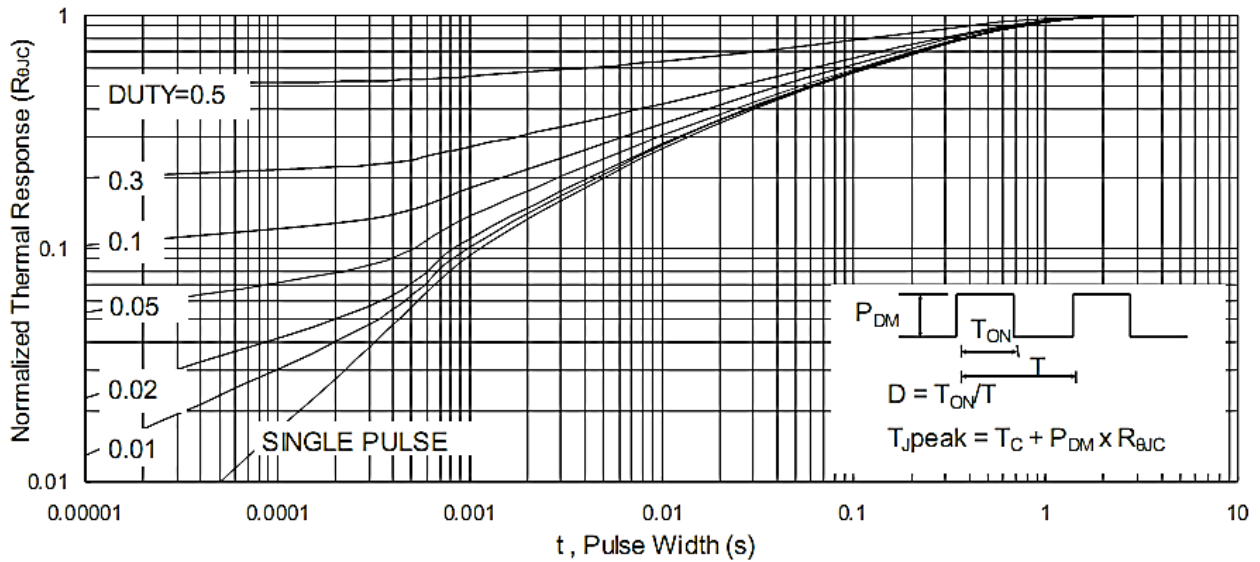


Fig.9 Normalized Maximum Transient Thermal Impedance

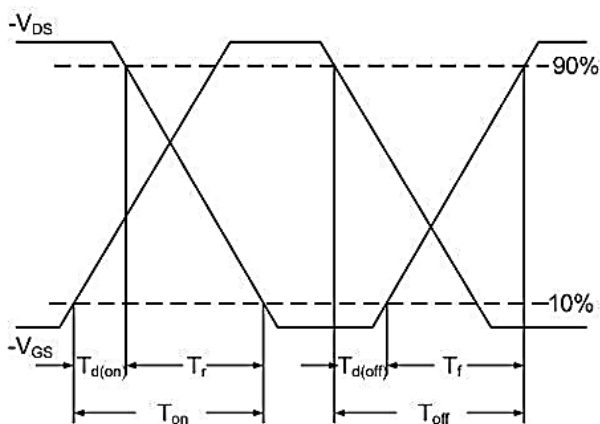


Fig.10 Switching Time Waveform

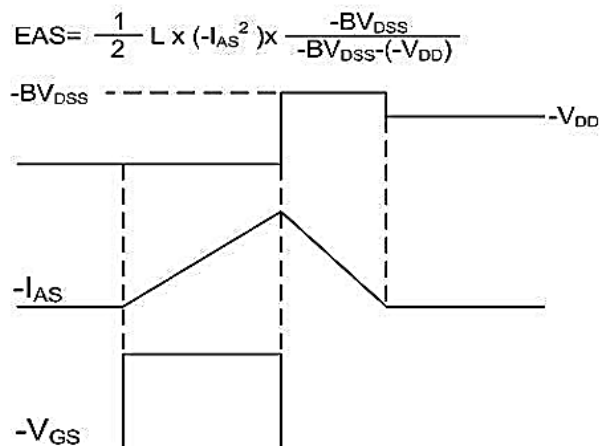
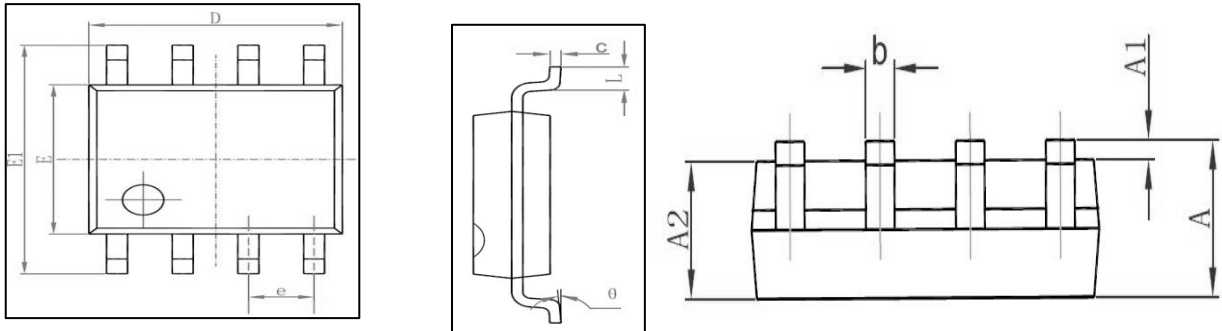
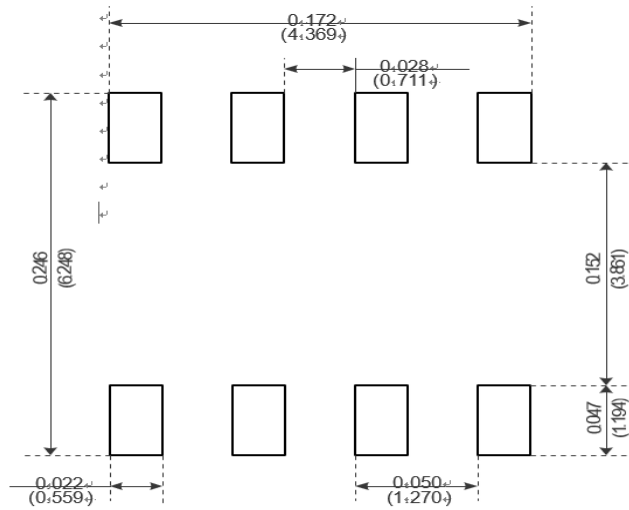


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

**NOTICE**

Leiditech reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Leiditech does not assume any liability arising out of the application or use of any product described herein.